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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

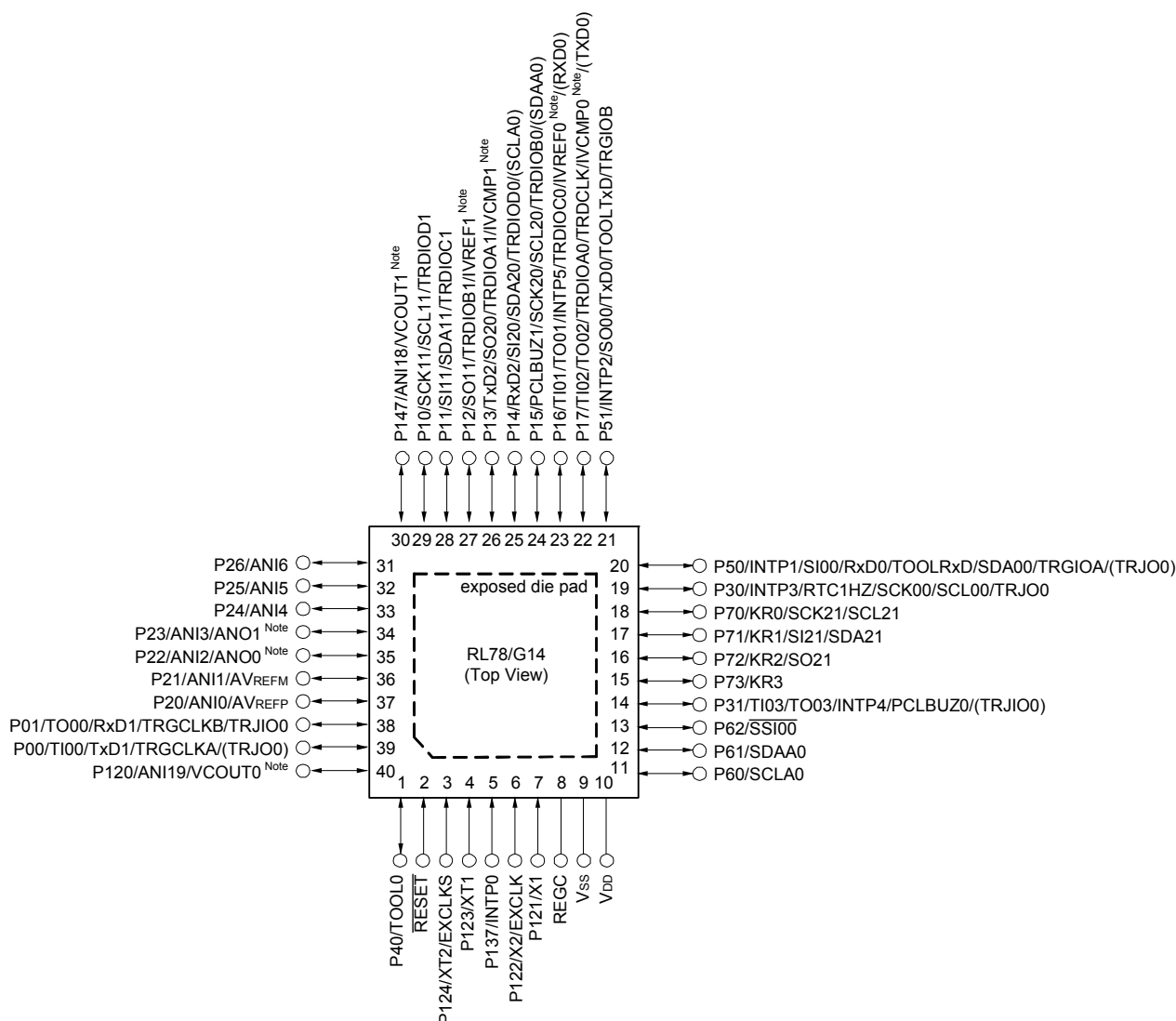
### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104llafa-50">https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104llafa-50</a>

### 1.3.4 40-pin products

- 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



**Note** Mounted on the 96 KB or more code flash memory products.

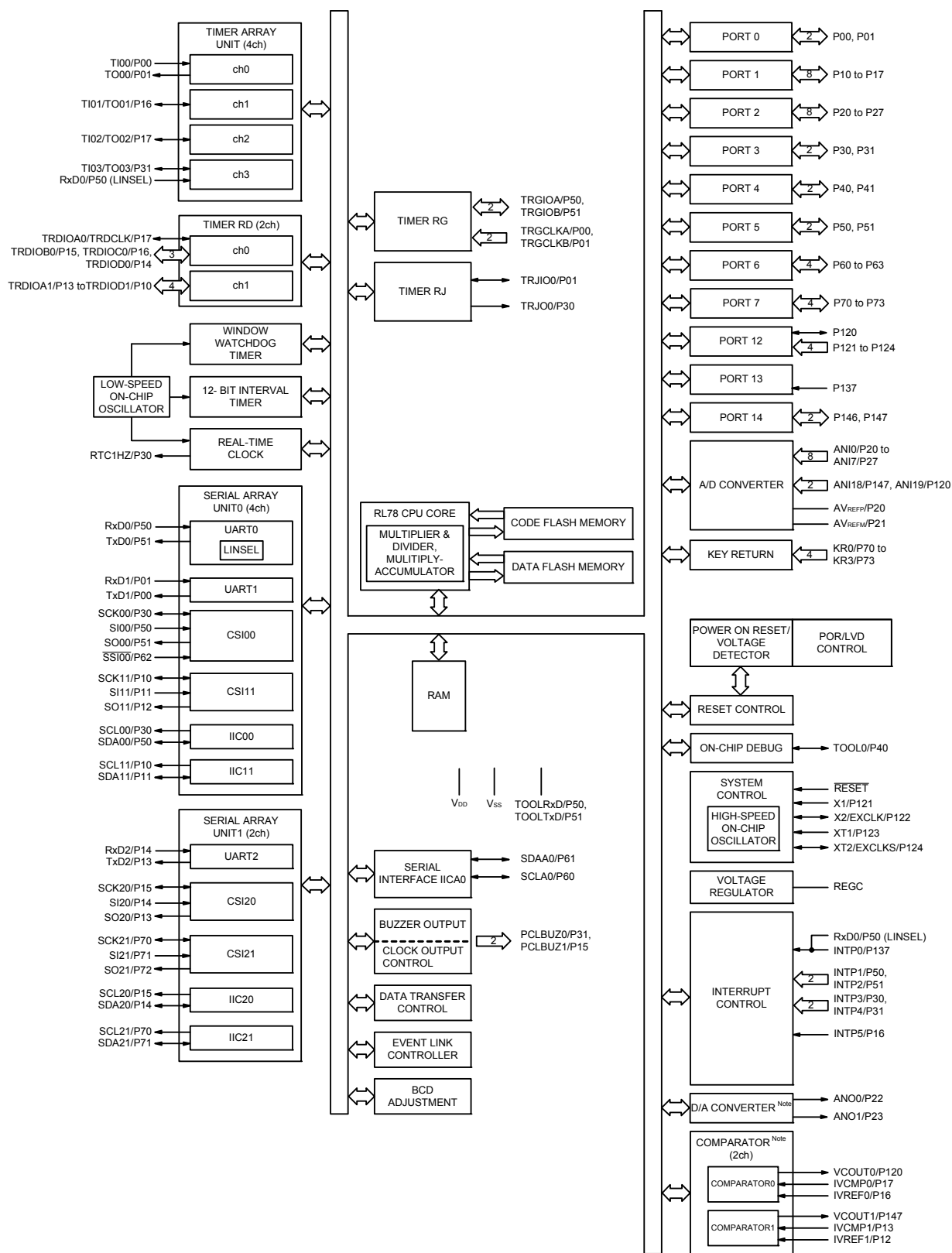
**Caution** Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

**Remark 1.** For pin identification, see 1.4 Pin Identification.

**Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

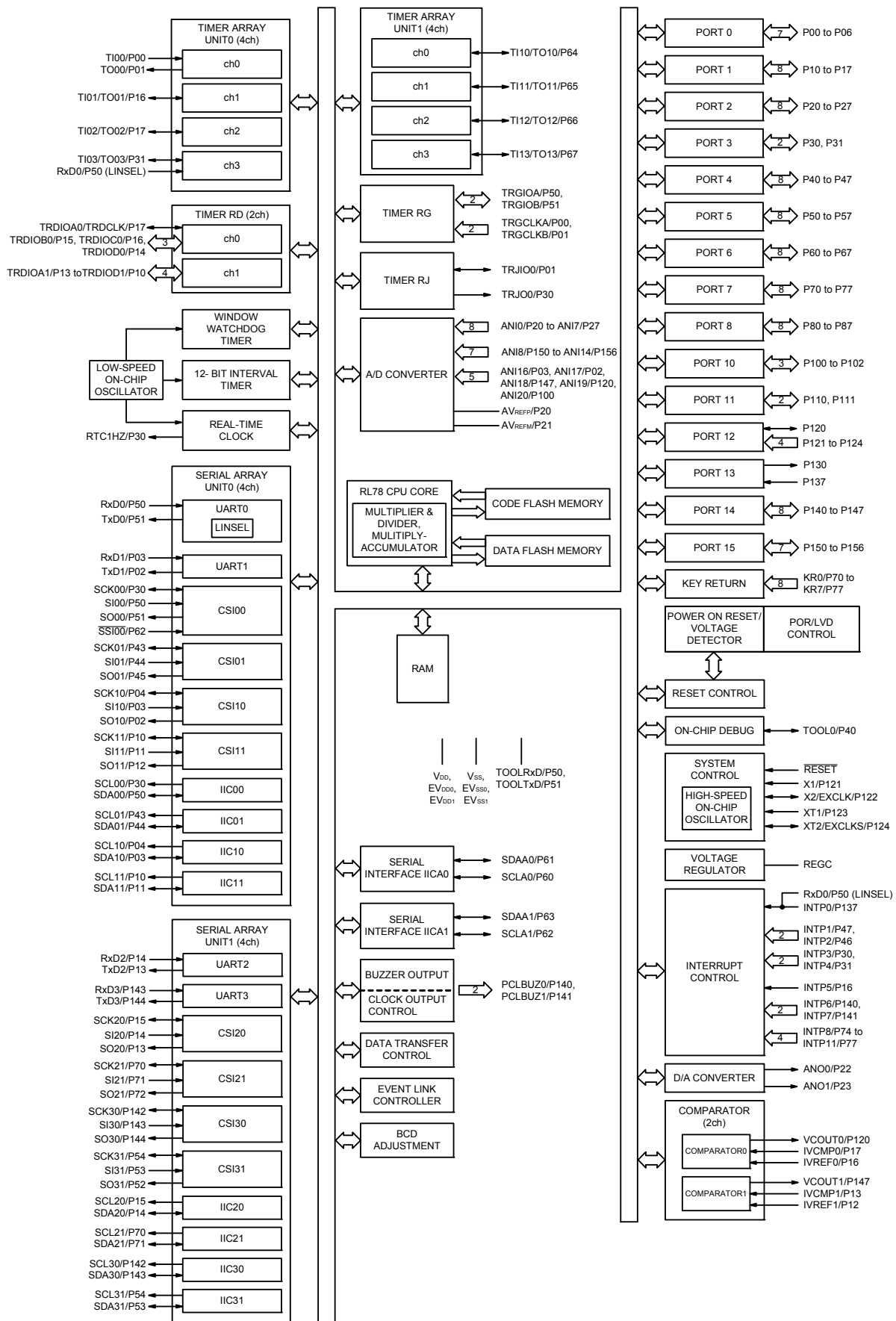
**Remark 3.** It is recommended to connect an exposed die pad to Vss.

### 1.5.5 44-pin products



**Note** Mounted on the 96 KB or more code flash memory products.

## 1.5.10 100-pin products



[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 96 KB to 256 KB)]

**Caution** This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		30-pin	32-pin	36-pin	40-pin
		R5F104Ax (x = F, G)	R5F104Bx (x = F, G)	R5F104Cx (x = F, G)	R5F104Ex (x = F to H)
Code flash memory (KB)		96 to 128	96 to 128	96 to 128	96 to 192
Data flash memory (KB)		8	8	8	8
RAM (KB)		12 to 16 Note	12 to 16 Note	12 to 16 Note	12 to 20 Note
Address space		1 MB			
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz ( $V_{DD} = 2.7$ to $5.5$ V), HS (high-speed main) mode: 1 to 16 MHz ( $V_{DD} = 2.4$ to $5.5$ V), LS (low-speed main) mode: 1 to 8 MHz ( $V_{DD} = 1.8$ to $5.5$ V), LV (low-voltage main) mode: 1 to 4 MHz ( $V_{DD} = 1.6$ to $5.5$ V)			
	High-speed on-chip oscillator clock ( $f_{IH}$ )	HS (high-speed main) mode: 1 to 32 MHz ( $V_{DD} = 2.7$ to $5.5$ V), HS (high-speed main) mode: 1 to 16 MHz ( $V_{DD} = 2.4$ to $5.5$ V), LS (low-speed main) mode: 1 to 8 MHz ( $V_{DD} = 1.8$ to $5.5$ V), LV (low-voltage main) mode: 1 to 4 MHz ( $V_{DD} = 1.6$ to $5.5$ V)			
Subsystem clock		—			XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz
Low-speed on-chip oscillator clock		15 kHz (TYP.): $V_{DD} = 1.6$ to $5.5$ V			
General-purpose register		8 bits $\times$ 32 registers (8 bits $\times$ 8 registers $\times$ 4 banks)			
Minimum instruction execution time		0.03125 $\mu$ s (High-speed on-chip oscillator clock: $f_{IH} = 32$ MHz operation)			
		0.05 $\mu$ s (High-speed system clock: $f_{MX} = 20$ MHz operation)			
		—			30.5 $\mu$ s (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)
Instruction set		<ul style="list-style-type: none"> <li>• Data transfer (8/16 bits)</li> <li>• Adder and subtractor/logical operation (8/16 bits)</li> <li>• Multiplication (8 bits <math>\times</math> 8 bits, 16 bits <math>\times</math> 16 bits), Division (16 bits <math>\div</math> 16 bits, 32 bits <math>\div</math> 32 bits)</li> <li>• Multiplication and Accumulation (16 bits <math>\times</math> 16 bits <math>\div</math> 32 bits)</li> <li>• Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.</li> </ul>			
I/O port	Total	26	28	32	36
	CMOS I/O	21	22	26	28
	CMOS input	3	3	3	5
	CMOS output	—	—	—	—
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 13 channels PWM outputs: 9 channels			
	RTC output	—			1 • 1 Hz (subsystem clock: $f_{SUB} = 32.768$ kHz)

(Note is listed on the next page.)

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(3/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	0.8 EVDD0		EVDD0	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2	EVDD0	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0	EVDD0	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5	EVDD0	V
	VIH3	P20 to P27, P150 to P156	0.7 VDD		VDD	V
	VIH4	P60 to P63	0.7 EVDD0		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EXCLKS, RESET	0.8 VDD		VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0	0.8	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0	0.5	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0	0.32	V
	VIL3	P20 to P27, P150 to P156	0		0.3 VDD	V
	VIL4	P60 to P63	0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS, RESET	0		0.2 VDD	V

**Caution** The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

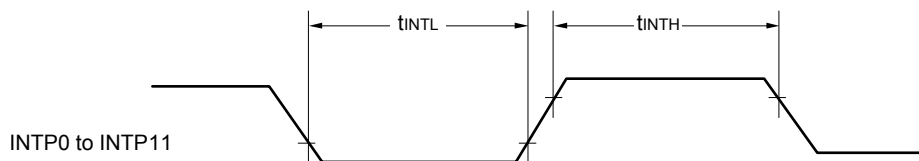
**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

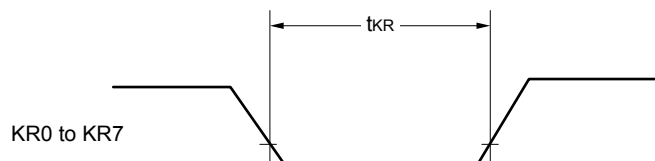
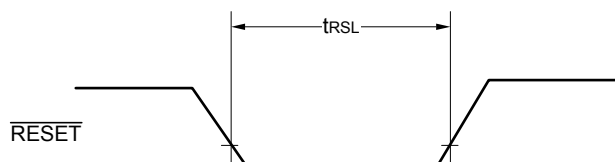
(2/2)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tTDIH, tTDIL	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1		3/fCLK			ns
Timer RD forced cutoff signal input low-level width	tTDSIL	P130/INTP0	2MHz < fCLK ≤ 32 MHz	1			μs
			fCLK ≤ 2 MHz	1/fCLK + 1			
Timer RG input high-level width, low-level width	tTGIH, tTGIL	TRGIOA, TRGIOB		2.5/fCLK			ns
TO00 to TO03, TO10 to TO13, TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency	fTO	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.6 V ≤ EVDD0 ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	fPCL	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
Interrupt input high-level width, low-level width	tINTH, tINTL	INTP0	1.6 V ≤ VDD ≤ 5.5 V	1			μs
		INTP1 to INTP11	1.6 V ≤ EVDD0 ≤ 5.5 V	1			μs
Key interrupt input low-level width	tKR	KR0 to KR7	1.8 V ≤ EVDD0 ≤ 5.5 V	250			ns
			1.6 V ≤ EVDD0 < 1.8 V	1			μs
RESET low-level width	tRSL			10			μs

## Interrupt Request Input Timing



## Key Interrupt Input Timing

 $\overline{\text{RESET}}$  Input Timing

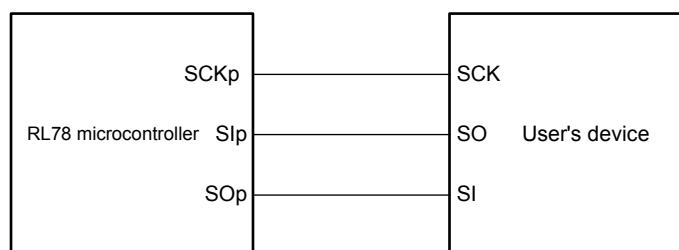


**(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)****(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)****(2/2)**

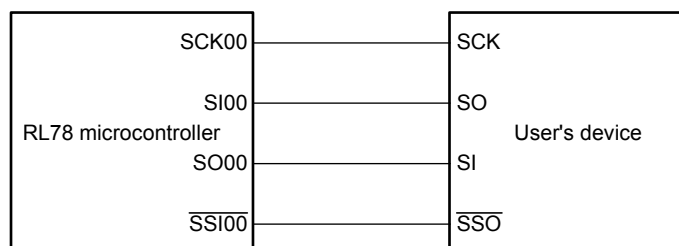
Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SSI00 setup time	tSSIK	DAPmn = 0	2.7 V ≤ EVDD0 ≤ 5.5 V	120		120		120	ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	200		200		200	ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	400		400		400	ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		400		400	ns
		DAPmn = 1	2.7 V ≤ EVDD0 ≤ 5.5 V	1/fMCK + 120		1/fMCK + 120		1/fMCK + 120	ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	1/fMCK + 200		1/fMCK + 200		1/fMCK + 200	ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	1/fMCK + 400		1/fMCK + 400		1/fMCK + 400	ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		1/fMCK + 400		1/fMCK + 400	ns
SSI00 hold time	tKSSI	DAPmn = 0	2.7 V ≤ EVDD0 ≤ 5.5 V	1/fMCK + 120		1/fMCK + 120		1/fMCK + 120	ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	1/fMCK + 200		1/fMCK + 200		1/fMCK + 200	ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	1/fMCK + 400		1/fMCK + 400		1/fMCK + 400	ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		1/fMCK + 400		1/fMCK + 400	ns
		DAPmn = 1	2.7 V ≤ EVDD0 ≤ 5.5 V	120		120		120	ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	200		200		200	ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	400		400		400	ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		400		400	ns

**Caution** Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

**Remark** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

**CSI mode connection diagram (during communication at same potential)**

**CSI mode connection diagram (during communication at same potential)**  
**(Slave Transmission of slave select input function (CSI00))**



**Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

**Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

**(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)****(TA = -40 to +85°C, 1.8 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)****(3/3)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp↓) Note 1	tSIK1	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ	44		110		110		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V Note 2, Cb = 30 pF, Rb = 5.5 kΩ	110		110		110		ns
Slp hold time (from SCKp↓) Note 1	tKSI1	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V Note 2, Cb = 30 pF, Rb = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 1	tKSO1	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ		25		25		25	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V Note 2, Cb = 30 pF, Rb = 5.5 kΩ		25		25		25	ns

**Note 1.** When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.**Note 2.** Use it with EVDD0 ≥ Vb.

**Caution** Select the TTL input buffer for the Slp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

## 2.6 Analog Characteristics

### 2.6.1 A/D converter characteristics

#### Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AV <sub>REFP</sub> Reference voltage (-) = AV <sub>REFM</sub>	Reference voltage (+) = V <sub>DD</sub> Reference voltage (-) = V <sub>SS</sub>	Reference voltage (+) = V <sub>BGR</sub> Reference voltage (-) = AV <sub>REFM</sub>
ANI0 to ANI14	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI20	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1).		—

(1) When reference voltage (+) = AV<sub>REFP</sub>/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV<sub>REFM</sub>/ANI1 (ADREFM = 1), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V ≤ AV<sub>REFP</sub> ≤ V<sub>DD</sub> ≤ 5.5 V, V<sub>SS</sub> = 0 V, Reference voltage (+) = AV<sub>REFP</sub>, Reference voltage (-) = AV<sub>REFM</sub> = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error Note 1	AINL	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.8 V ≤ AV <sub>REFP</sub> ≤ 5.5 V	1.2	±3.5	LSB
			1.6 V ≤ AV <sub>REFP</sub> ≤ 5.5 V Note 4	1.2	±7.0	LSB
Conversion time	t <sub>CONV</sub>	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	2.125	39	μs
			2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	3.1875	39	μs
			1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V	17	39	μs
			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	57	95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	2.375	39	μs
			2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	3.5625	39	μs
			2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V	17	39	μs
Zero-scale error Notes 1, 2	E <sub>ZS</sub>	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.8 V ≤ AV <sub>REFP</sub> ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV <sub>REFP</sub> ≤ 5.5 V Note 4		±0.50	%FSR
Full-scale error Notes 1, 2	E <sub>FS</sub>	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.8 V ≤ AV <sub>REFP</sub> ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV <sub>REFP</sub> ≤ 5.5 V Note 4		±0.50	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.8 V ≤ AV <sub>REFP</sub> ≤ 5.5 V		±2.5	LSB
			1.6 V ≤ AV <sub>REFP</sub> ≤ 5.5 V Note 4		±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.8 V ≤ AV <sub>REFP</sub> ≤ 5.5 V		±1.5	LSB
			1.6 V ≤ AV <sub>REFP</sub> ≤ 5.5 V Note 4		±2.0	LSB
Analog input voltage	V <sub>AIN</sub>	ANI2 to ANI14	0		AV <sub>REFP</sub>	V
		Internal reference voltage (2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V, HS (high-speed main) mode)			V <sub>BGR</sub> Note 5	V
		Temperature sensor output voltage (2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V, HS (high-speed main) mode)			V <sub>TMPS25</sub> Note 5	V

**Note 1.** Excludes quantization error (±1/2 LSB).

**Note 2.** This value is indicated as a ratio (%FSR) to the full-scale value.

**Note 3.** When AV<sub>REFP</sub> < V<sub>DD</sub>, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.

**Note 4.** Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

**Note 5.** Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

- Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or VSS, EVSS0, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3.** When high-speed system clock and subsystem clock are stopped.
- Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
- HS (high-speed main) mode:  $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$  @1 MHz to 32 MHz  
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$  @1 MHz to 16 MHz

**Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

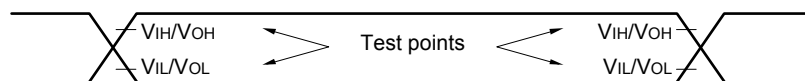
**Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)

**Remark 3.** fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)

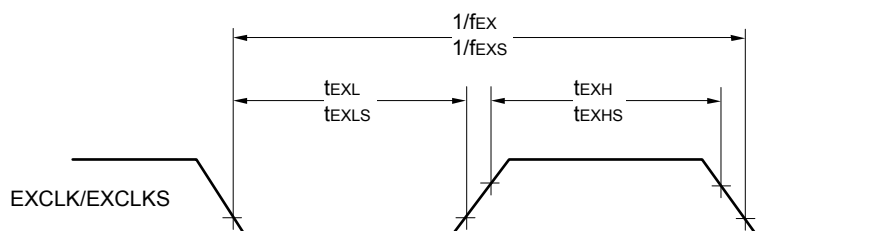
**Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)

**Remark 5.** Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

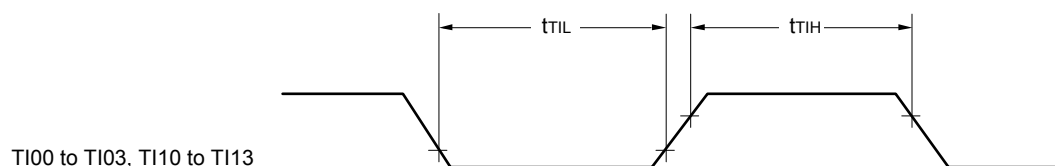
## AC Timing Test Points



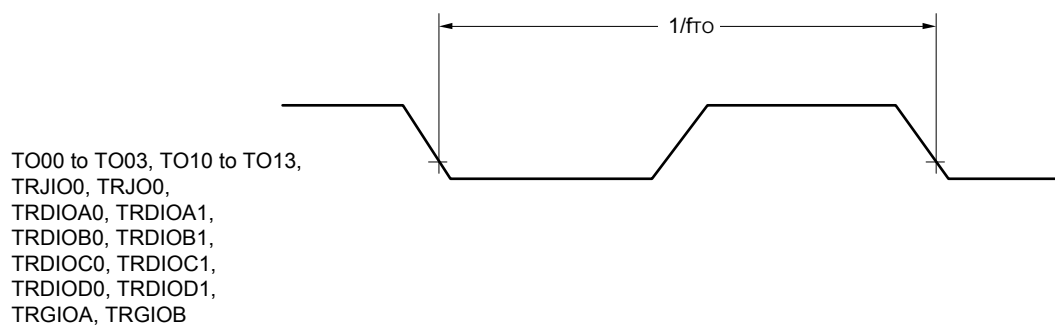
## External System Clock Timing



## TI/TO Timing



TI00 to TI03, TI10 to TI13



TO00 to TO03, TO10 to TO13,  
TRJIO0, TRJO0,  
TRDIOA0, TRDIOA1,  
TRDIOB0, TRDIOB1,  
TRDIOC0, TRDIOC1,  
TRDIOD0, TRDIOD1,  
TRGIOA, TRGIOB

**(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)****(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)****(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
Transfer rate		transmission	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	Note 1	bps
			Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 1.4 kΩ, Vb = 2.7 V	2.6 Note 2	Mbps
			2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	Note 3	bps
			Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 2.7 kΩ, Vb = 2.3 V	1.2 Note 4	Mbps
			2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	Note 5	bps
			Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 5.5 kΩ, Vb = 1.6 V	0.43 Note 6	Mbps

**Note 1.** The smaller maximum transfer rate derived by using fmCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EVDD0 ≤ 5.5 V and 2.7 V ≤ Vb ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

\* This value is the theoretical value of the relative difference between the transmission and reception sides

**Note 2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

**Note 3.** The smaller maximum transfer rate derived by using fmCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EVDD0 < 4.0 V and 2.3 V ≤ Vb ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

\* This value is the theoretical value of the relative difference between the transmission and reception sides

**Note 4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

## (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	24 MHz < fMCK	28/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	24/fMCK	ns
			8 MHz < fMCK ≤ 20 MHz	20/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK	ns
			fMCK ≤ 4 MHz	12/fMCK	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	24 MHz < fMCK	40/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	32/fMCK	ns
			16 MHz < fMCK ≤ 20 MHz	28/fMCK	ns
			8 MHz < fMCK ≤ 16 MHz	24/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK	ns
			fMCK ≤ 4 MHz	12/fMCK	ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	24 MHz < fMCK	96/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	72/fMCK	ns
			16 MHz < fMCK ≤ 20 MHz	64/fMCK	ns
			8 MHz < fMCK ≤ 16 MHz	52/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	32/fMCK	ns
			fMCK ≤ 4 MHz	20/fMCK	ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	tkCY2/2 - 24		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	tkCY2/2 - 36		ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	tkCY2/2 - 100		ns
Slp setup time (to SCKp↑) Note 2	tsIK2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	1/fMCK + 40		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	1/fMCK + 40		ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	1/fMCK + 60		ns
Slp hold time (from SCKp↑) Note 3	tsIS2		1/fMCK + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tkSO2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ		2/fMCK + 240	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ		2/fMCK + 428	ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V, Cb = 30 pF, Rv = 5.5 kΩ		2/fMCK + 1146	ns

(Notes, Caution, and Remarks are listed on the next page.)

(2) When reference voltage (+) =  $AV_{REFP}/ANI0$  ( $ADREFP1 = 0$ ,  $ADREFP0 = 1$ ), reference voltage (-) =  $AV_{REFM}/ANI1$  ( $ADREFM = 1$ ), target pin: ANI16 to ANI20

( $T_A = -40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$ ,  $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$ ,

$V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$ , Reference voltage (+) =  $AV_{REFP}$ , Reference voltage (-) =  $AV_{REFM} = 0\text{ V}$ )

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		1.2	$\pm 5.0$	LSB
Conversion time	$t_{CONV}$	10-bit resolution Target ANI pin: ANI16 to ANI20	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	$\mu\text{s}$
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	$\mu\text{s}$
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	$\mu\text{s}$
Zero-scale error Notes 1, 2	$E_{ZS}$	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 0.35$	%FSR
Full-scale error Notes 1, 2	$E_{FS}$	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 0.35$	%FSR
Integral linearity error Note 1	ILE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 3.5$	LSB
Differential linearity error Note 1	DLE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			$\pm 2.0$	LSB
Analog input voltage	$V_{AIN}$	ANI16 to ANI20		0		$AV_{REFP}$ and $EV_{DD0}$	V

**Note 1.** Excludes quantization error ( $\pm 1/2$  LSB).

**Note 2.** This value is indicated as a ratio (%FSR) to the full-scale value.

**Note 3.** When  $EV_{DD0} \leq AV_{REFP} \leq V_{DD}$ , the MAX. values are as follows.

Overall error: Add  $\pm 1.0$  LSB to the MAX. value when  $AV_{REFP} = V_{DD}$ .  
 Zero-scale error/Full-scale error: Add  $\pm 0.05\%$ FSR to the MAX. value when  $AV_{REFP} = V_{DD}$ .  
 Integral linearity error/ Differential linearity error: Add  $\pm 0.5$  LSB to the MAX. value when  $AV_{REFP} = V_{DD}$ .

**Note 4.** When  $AV_{REFP} < EV_{DD0} \leq V_{DD}$ , the MAX. values are as follows.

Overall error: Add  $\pm 4.0$  LSB to the MAX. value when  $AV_{REFP} = V_{DD}$ .  
 Zero-scale error/Full-scale error: Add  $\pm 0.20\%$ FSR to the MAX. value when  $AV_{REFP} = V_{DD}$ .  
 Integral linearity error/ Differential linearity error: Add  $\pm 2.0$  LSB to the MAX. value when  $AV_{REFP} = V_{DD}$ .



**3.6.2 Temperature sensor characteristics/internal reference voltage characteristic****( $T_A = -40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ ,  $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$ , HS (high-speed main) mode)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, $T_A = +25^\circ\text{C}$		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/ $^\circ\text{C}$
Operation stabilization wait time	tAMP		5			$\mu\text{s}$

**3.6.3 D/A converter characteristics****( $T_A = -40$  to  $+105^\circ\text{C}$ ,  $2.4\text{ V} \leq EV_{SS0} = EV_{SS1} \leq V_{DD} \leq 5.5\text{ V}$ ,  $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$ )**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 M $\Omega$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			$\pm 2.5$	LSB
		Rload = 8 M $\Omega$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			$\pm 2.5$	LSB
Settling time	tSET	Cload = 20 pF	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			3	$\mu\text{s}$
			$2.4\text{ V} \leq V_{DD} < 2.7\text{ V}$			6	$\mu\text{s}$

### 3.6.6 LVD circuit characteristics

#### (1) Reset Mode and Interrupt Mode

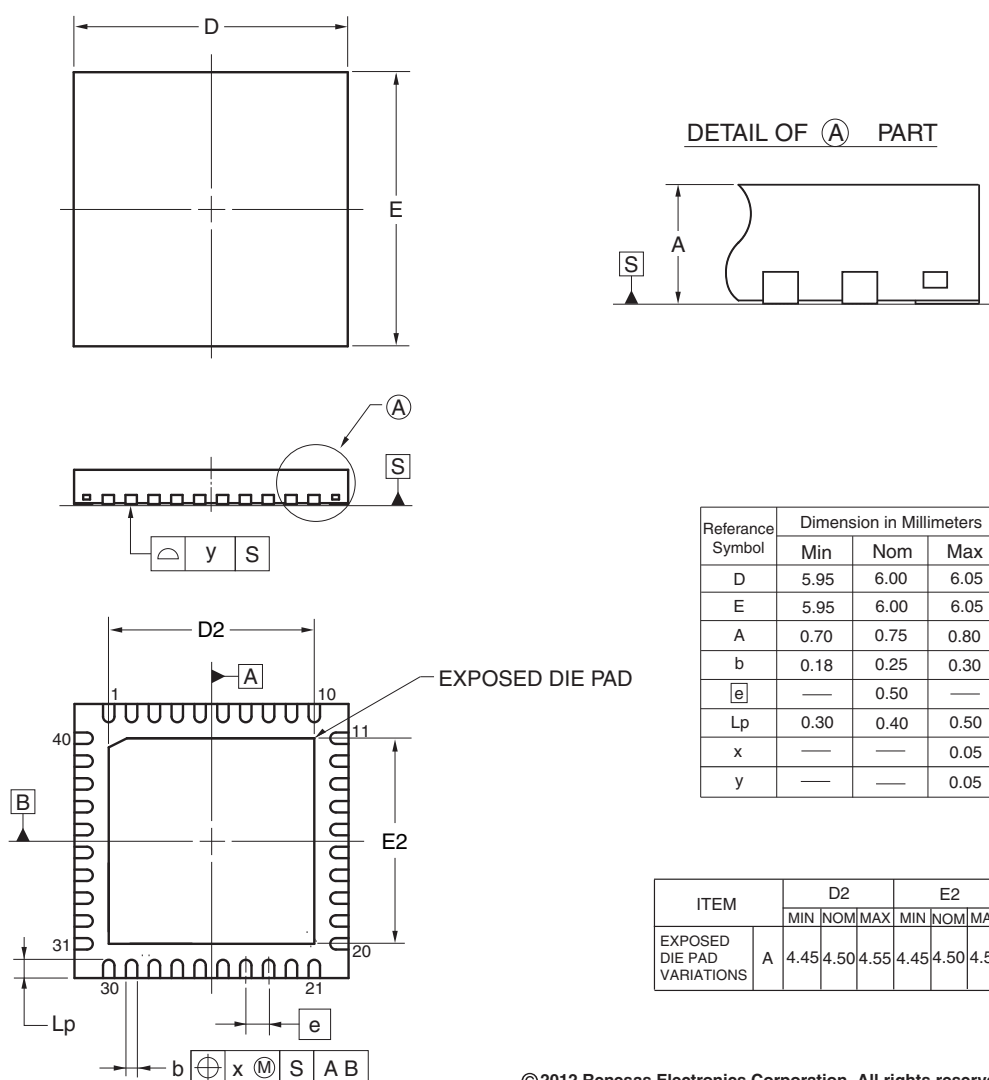
(TA = -40 to +105°C, VPDR ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection threshold	Supply voltage level	VLVD0	Rising edge	3.90	4.06	4.22	V
			Falling edge	3.83	3.98	4.13	V
		VLVD1	Rising edge	3.60	3.75	3.90	V
			Falling edge	3.53	3.67	3.81	V
		VLVD2	Rising edge	3.01	3.13	3.25	V
			Falling edge	2.94	3.06	3.18	V
		VLVD3	Rising edge	2.90	3.02	3.14	V
			Falling edge	2.85	2.96	3.07	V
		VLVD4	Rising edge	2.81	2.92	3.03	V
			Falling edge	2.75	2.86	2.97	V
		VLVD5	Rising edge	2.70	2.81	2.92	V
			Falling edge	2.64	2.75	2.86	V
		VLVD6	Rising edge	2.61	2.71	2.81	V
			Falling edge	2.55	2.65	2.75	V
		VLVD7	Rising edge	2.51	2.61	2.71	V
			Falling edge	2.45	2.55	2.65	V
Minimum pulse width		tLW		300			μs
Detection delay time						300	μs

#### 4.4 40-pin products

R5F104EAANA, R5F104ECANA, R5F104EDANA, R5F104EEANA, R5F104EFANA, R5F104EGANA,  
 R5F104EHANA  
 R5F104EADNA, R5F104ECDNA, R5F104EDDNA, R5F104EEDNA, R5F104EFDNA, R5F104EGDNA,  
 R5F104EHDNA  
 R5F104EAGNA, R5F104ECGNA, R5F104EDGNA, R5F104EEGNA, R5F104EFGNA, R5F104EGGNA,  
 R5F104EHGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-4	0.09

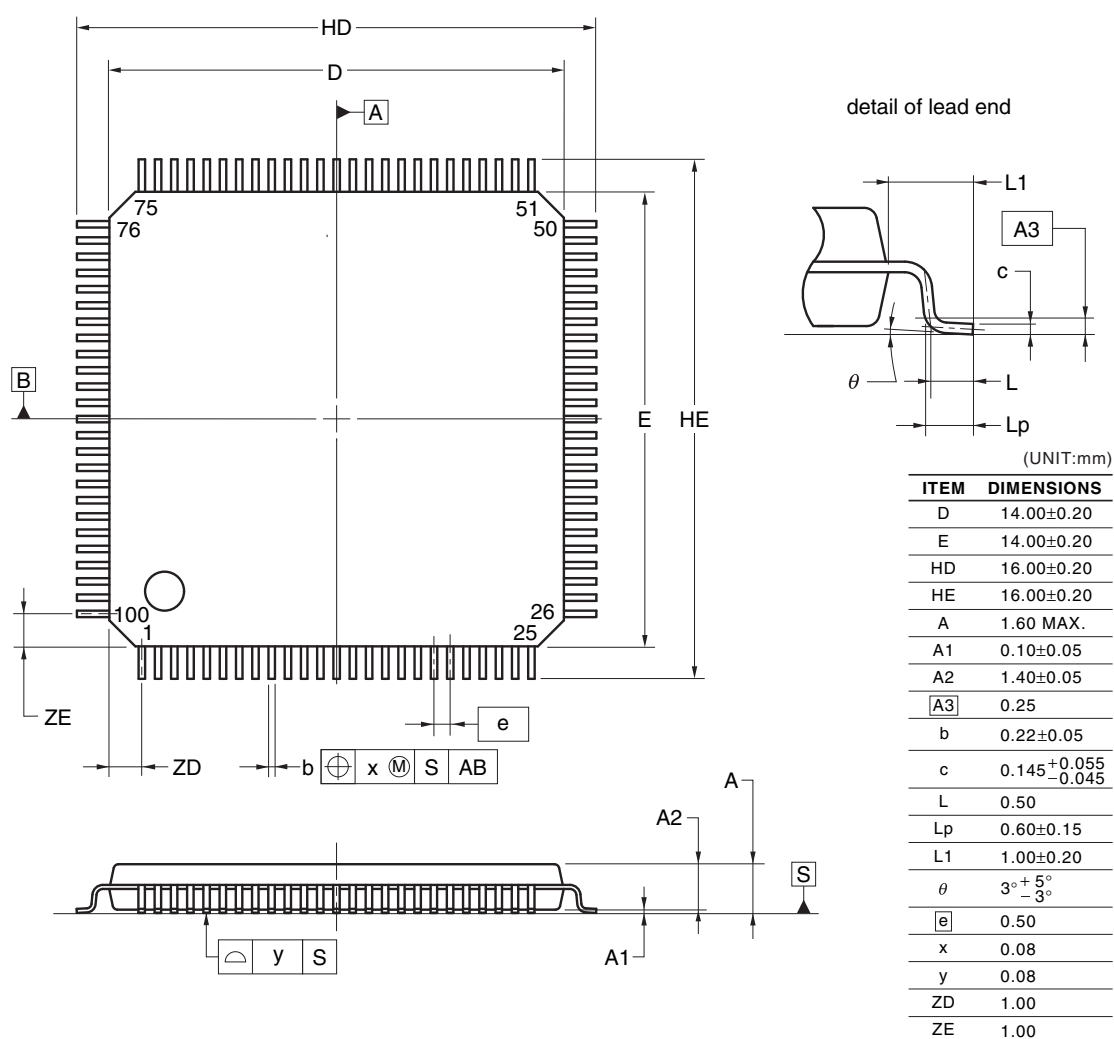


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### 4.10 100-pin products

R5F104PFAFB, R5F104PGAFA, R5F104PHAFA, R5F104PJAFB  
 R5F104PFDFA, R5F104PGDFA, R5F104PHDFA, R5F104PJDFB  
 R5F104PFGFB, R5F104PGGFB, R5F104PHGFB, R5F104PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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